

COMPLIANCE

TSM40N03PQ56

30V N-Channel Power MOSFET

 $R_{DS(on)}(m\Omega)$

4.5 @ V_{GS}=10V

5.8 @ V_{GS}=4.5V

 $I_D(A)$

19

16

PRODUCT SUMMARY

V_{DS} (V)

30

PDFN56

Pin Definition:			
1. Source	8. Drain		
2. Source	7. Drain		
3. Source	6. Drain		
4. Gate	5. Drain		

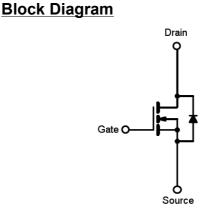
Features

- Advanced Trench Technology
- Low On-Resistance
- Low gate charge typical @ 12nC (Typ.)
- Low Crss typical @ 140pF (Typ.)

Ordering Information

Part No.	Package	Packing
TSM40N03PQ56 RLG	PDFN56	2.5Kpcs / 13" Reel

Note: "G" denote for Halogen Free Product



N-Channel MOSFET

Absolute Maximum Ratings (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	30	V	
Gate-Source Voltage		V _{GS}	±20	V	
Continuous Drain Current	T _C =25°C		40		
	T _C =70°C		40	А	
	T _A =25°C	l _D	31		
	T _A =70°C		25		
Drain Current-Pulsed Note 1		I _{DM}	100	А	
Avalanche Current, L=0.5mH		I _{AS} , I _{AR}	38	А	
Avalanche Energy, L=0.5mH		E _{AS} , E _{AR}	72	mJ	
Maximum Power Dissipation	T _C =25°C		36		
	T _C =70°C		23	W	
	T _A =25°C	P _D	4.2		
	T _A =70°C		2.7		
Storage Temperature Range		T _{STG}	-55 to +150	°C	
Operating Junction Temperature Range		TJ	-55 to +150	°C	

* Limited by maximum junction temperature

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	R⊖ _{JC}	3.5	°C/W
Thermal Resistance - Junction to Ambient	Rθ _{JA}	30	°C/W

Notes: Surface mounted on FR4 board t \leq 10sec



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Electrical Specifications (Ta = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static				•	•	
Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250µA	BV_{DSS}	30			V
Drein Course On State Desistance	V _{GS} = 10V, I _D = 19A	_		3.5	4.5	mΩ
Drain-Source On-State Resistance	V _{GS} = 4.5V, I _D = 16A	R _{DS(ON)}		4.6	5.8	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V _{GS(TH)}	1.15		2.2	V
Zero Gate Voltage Drain Current	V_{DS} = 24V, V_{GS} = 0V	I _{DSS}			1	μA
Gate Body Leakage	V_{GS} = ±20V, V_{DS} = 0V	I _{GSS}			±100	nA
Dynamic						
Total Gate Charge		Qg		12		nC
Gate-Source Charge	V _{DS} = 15V, I _D = 19A, V _{GS} = 4.5V	Q _{gs}		5.4		
Gate-Drain Charge		Q_gd		4.6		
Input Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	C _{iss}		1700		
Output Capacitance		C _{oss}		350		pF
Reverse Transfer Capacitance		C _{rss}		140		
Switching						
Turn-On Delay Time		t _{d(on)}		25		
Turn-On Rise Time	V _{GS} = 4.5V, V _{DS} = 15V,	t _r		20		
Turn-Off Delay Time	$R_G = 1\Omega$	t _{d(off)}		25		ns
Turn-Off Fall Time		t _f		15		
Drain-Source Diode Characteristic	s and Maximum Rating					
Drain-Source Diode Forward Voltage	V _{GS} =0V, I _S =10A	V _{SD}		0.8	1.2	V
Reverse Recovery Time	I _S = 10A, T _J =25 °C	t _{fr}		25		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q _{fr}		17		nC

Notes:

1. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

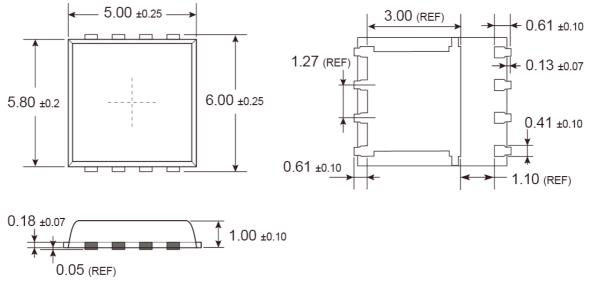
2. $R\theta_{JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R\theta_{JC}$ is guaranteed by design while $R\theta_{CA}$ is determined by the user's board design. $R\theta_{JA}$ shown below for single device operation on FR-4 in still air

3. The maximum current rating is limited by package.



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PDFN56 Mechanical Drawing



Unit: Millimeters



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